



ALPHA & OMEGA
SEMICONDUCTOR

AO6407

P-Channel Enhancement Mode Field Effect Transistor



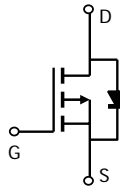
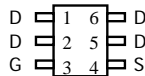
General Description

The AO6407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO6407 is Pb-free (meets ROHS & Sony 259 specifications). AO6407L is a Green Product ordering option. AO6407 and AO6407L are electrically identical.*

Features

- V_{DS} (V) = -20V
- I_D = -5 A (V_{GS} = -4.5V)
- $R_{DS(ON)} < 45m\Omega$ (V_{GS} = -4.5V)
- $R_{DS(ON)} < 60m\Omega$ (V_{GS} = -2.5V)
- $R_{DS(ON)} < 85m\Omega$ (V_{GS} = -1.8V)

TSOP6
Top View



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	-5.5	A
		$T_A=25^\circ\text{C}$	
	$T_A=70^\circ\text{C}$	-4.5	
Pulsed Drain Current ^B	I_{DM}	-30	
Power Dissipation ^A	P_D	2	W
		$T_A=25^\circ\text{C}$	
	$T_A=70^\circ\text{C}$	1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	47.5	62.5	$^\circ\text{C/W}$
		$t \leq 10\text{s}$		
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	74	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	37	50	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.3	-0.55	-1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$ $T_J=125^\circ\text{C}$		34 48	45 60	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-4\text{A}$		46	60	$\text{m}\Omega$
		$V_{GS}=-1.8\text{V}, I_D=-2\text{A}$		61	85	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-5\text{A}$	7	14		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.78	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$		1180		pF
C_{oss}	Output Capacitance			176		pF
C_{rSS}	Reverse Transfer Capacitance			142		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		15		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-5\text{A}$		13		nC
Q_{gs}	Gate Source Charge			1.2		nC
Q_{gd}	Gate Drain Charge			3.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, R_L=2.0\Omega,$ $R_{GEN}=3\Omega$		13.2		ns
t_r	Turn-On Rise Time			21		ns
$t_{D(off)}$	Turn-Off DelayTime			93		ns
t_f	Turn-Off Fall Time			46		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		43		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		21		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

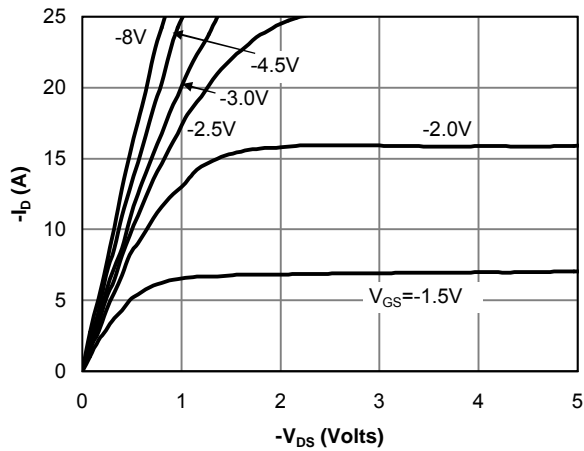


Fig 1: On-Region Characteristics

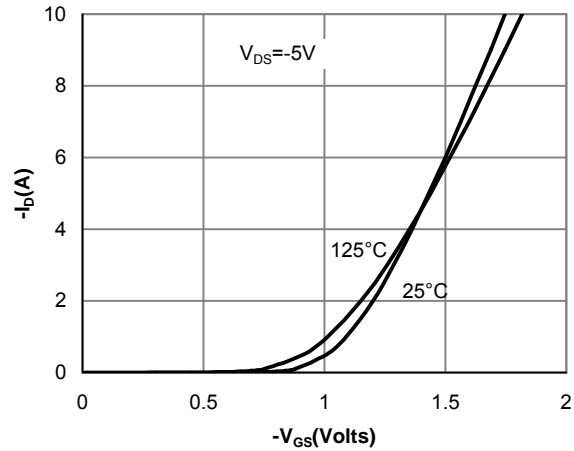


Figure 2: Transfer Characteristics

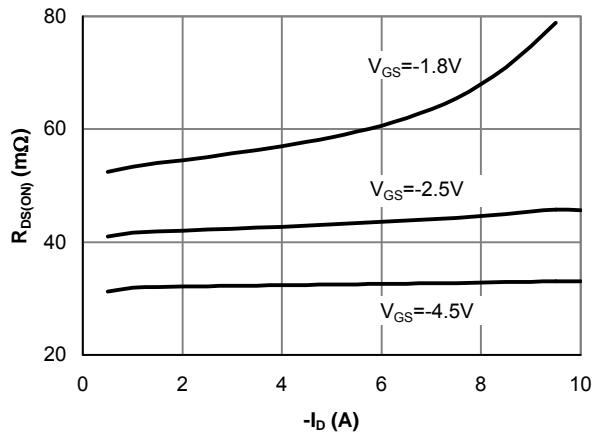


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

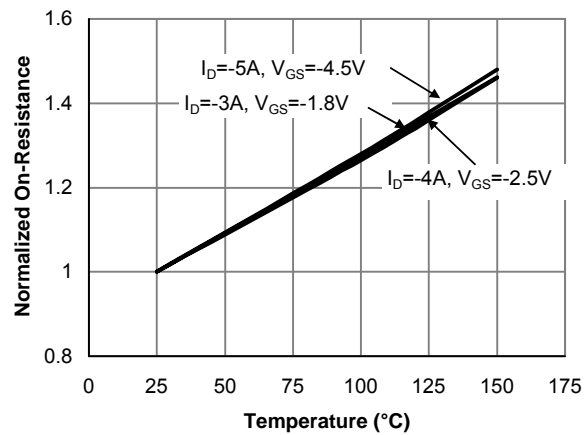


Figure 4: On-Resistance vs. Junction Temperature

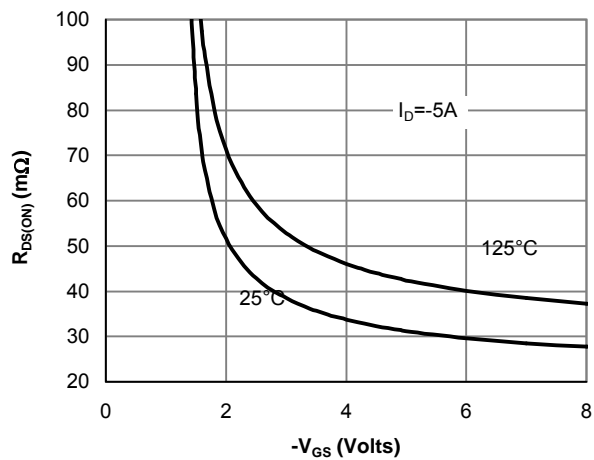


Figure 5: On-Resistance vs. Gate-Source Voltage

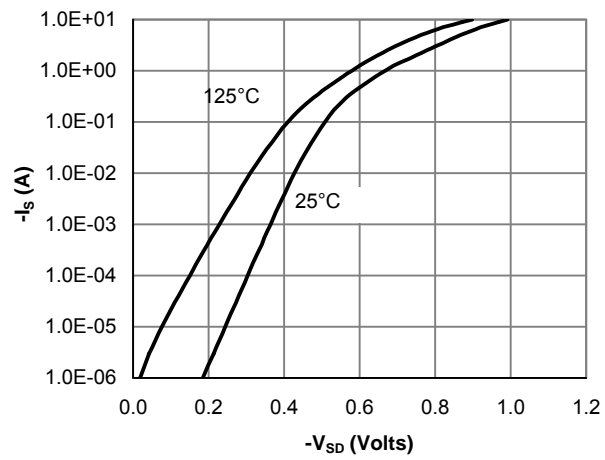


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

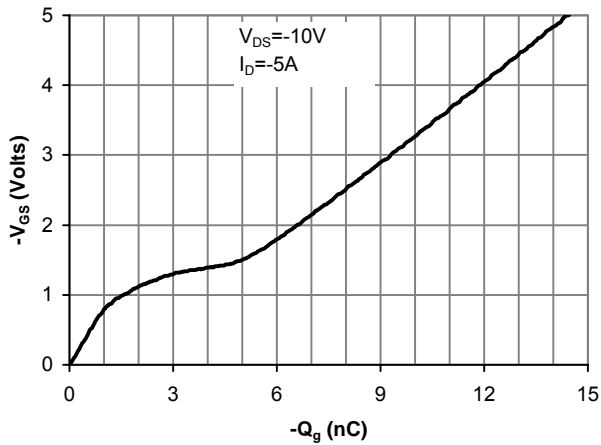


Figure 7: Gate-Charge Characteristics

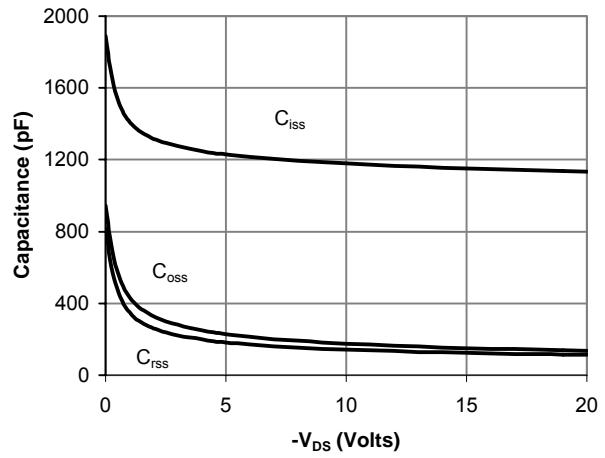


Figure 8: Capacitance Characteristics

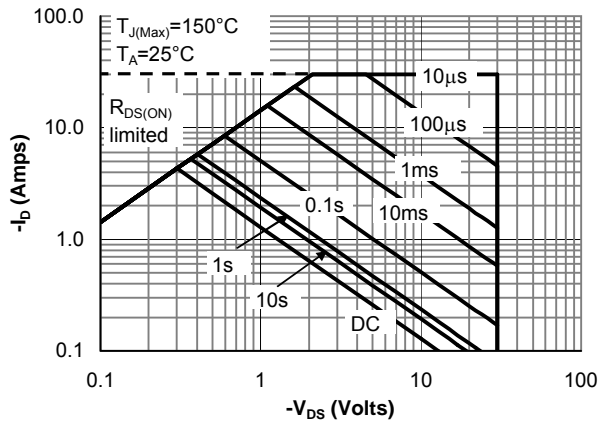


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

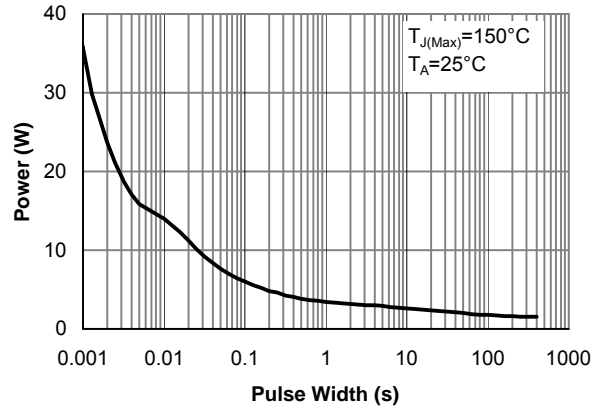


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

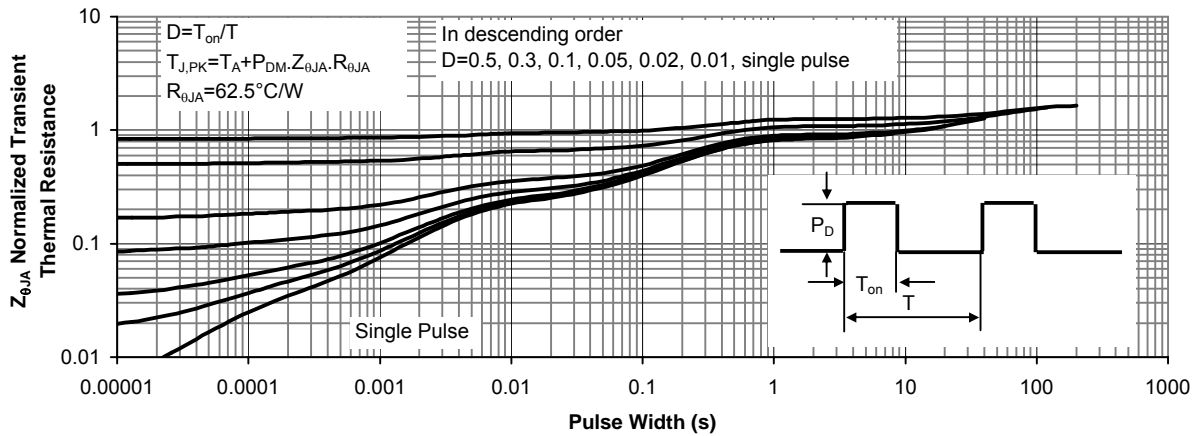


Figure 11: Normalized Maximum Transient Thermal Impedance